

P/N:YZPST-600B170E53 (YZPST-FF600R17ME4)

$V_{CE}=1700V$ $I_C=600A$

IGBT Power Module

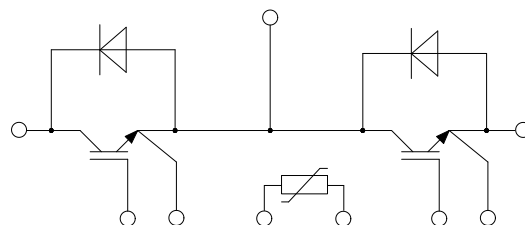
Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)



Features

- Low $V_{ce(sat)}$ with SPT+ IGBT technology
- $V_{ce(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- High short circuit capability(10us)
- Low inductance module structure
- Maximum junction temperature 175°C



Equivalent Circuit Schematic

● Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V$, $I_C=1mA$, $T_{vj}=25^{\circ}C$	1700	V
Continuous Collector Current	I_C	$T_c=100^{\circ}C$	600	A
Peak Collector Current	I_{CRM}	$I_{CRM}=2I_C$	1200	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation (IGBT-inverter)	P_{tot}	$T_c=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	4286	W

● IGBT Characteristics

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=24mA, T_{vj}=25^{\circ}C$	5.4	6.2	7.4	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1700V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=600A, V_{GE}=15V, T_{vj}=25^{\circ}C$		2.40	2.75	V
		$I_C=600A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.80		V
		$I_C=600A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.90		V
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		40.0		nF
Output Capacitance	C_{oes}			2.09		nF
Reverse Transfer Capacitance	C_{res}			1.44		nF
Turn-on Delay Time	$t_{d(on)}$	$I_C=600A$ $V_{CE}=900V$ $V_{GE}=\pm 15V$ $R_G=1.0\Omega$ $T_{vj}=25^{\circ}C$		180		ns
Rise Time	t_r			100		ns
Turn-off Delay Time	$t_{d(off)}$			300		ns
Fall Time	t_f			100		ns
Energy Dissipation During Turn-on Time	E_{on}			150		mJ
Energy Dissipation During Turn-off Time	E_{off}			100		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=600A$ $V_{CE}=900V$ $V_{GE}=\pm 15V$ $R_G=1.0\Omega$ $T_{vj}=125^{\circ}C$		190		ns
Rise Time	t_r			110		ns
Turn-off Delay Time	$t_{d(off)}$			350		ns
Fall Time	t_f			150		ns
Energy Dissipation During Turn-on Time	E_{on}			225		mJ
Energy Dissipation During Turn-off Time	E_{off}			160		mJ

Turn-on Delay Time	$t_{d(on)}$	$I_C = 600\text{ A}$ $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 1.0\Omega$ $T_{vj} = 150^\circ\text{C}$		210		ns
Rise Time	t_r			115		ns
Turn-off Delay Time	$t_{d(off)}$			360		ns
Fall Time	t_f			160		ns
Energy Dissipation During Turn-on Time	E_{on}			240		mJ
Energy Dissipation During Turn-off Time	E_{off}			185		mJ
SC Data	I_{sc}	$T_p \leq 10\mu\text{s}, V_{GE} = 15\text{ V},$ $T_{vj} = 150^\circ\text{C}, V_{cc} = 900\text{ V},$ $V_{CEM} \leq 1700\text{ V}$		1920		A

● Diode Characteristics

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode DC Forward Current	I_F	$T_c = 100^\circ\text{C}$		600		A
Diode Peak Forward Current	I_{FRM}	$I_{FRM} = 2I_F$		1200		A
Forward Voltage	V_F	$I_F = 600\text{ A}, T_{vj} = 25^\circ\text{C}$		1.85		V
		$I_F = 600\text{ A}, T_{vj} = 125^\circ\text{C}$		1.92		V
		$I_F = 600\text{ A}, T_{vj} = 150^\circ\text{C}$		1.90		V
Recovered Charge	Q_{rr}	$I_F = 600\text{ A}$		145		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 900\text{ V}$ $-di_F/dt = 6000\text{ A}/\mu\text{s}$		560		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 25^\circ\text{C}$		70		mJ
Recovered Charge	Q_{rr}	$I_F = 600\text{ A}$		240		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 900\text{ V}$ $-di_F/dt = 6000\text{ A}/\mu\text{s}$		635		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 125^\circ\text{C}$		135		mJ
Recovered Charge	Q_{rr}	$I_F = 600\text{ A}$		280		μC
Peak Reverse Recovery Current	I_{rr}	$V_R = 900\text{ V}$ $-di_F/dt = 6000\text{ A}/\mu\text{s}$		660		A
Reverse Recovery Energy	E_{rec}	$T_{vj} = 150^\circ\text{C}$		158		mJ

● NTC-Thermistor

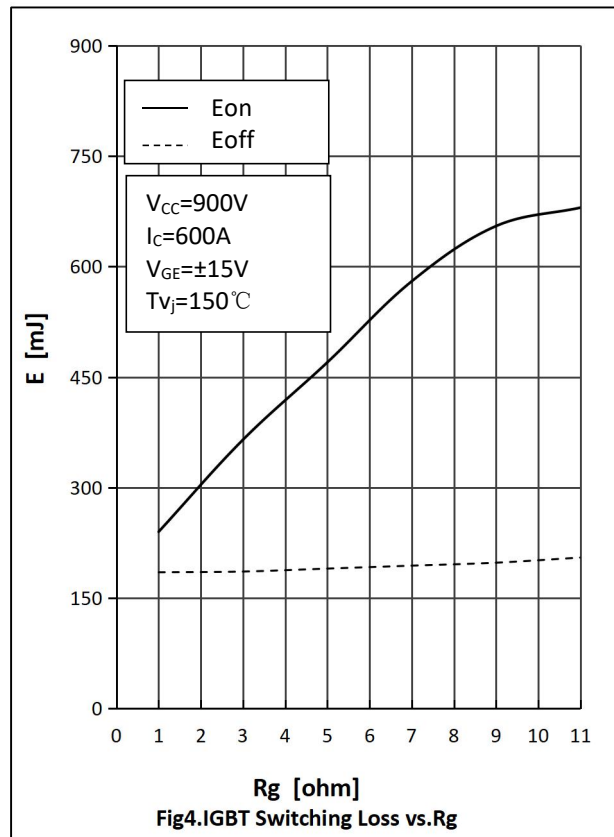
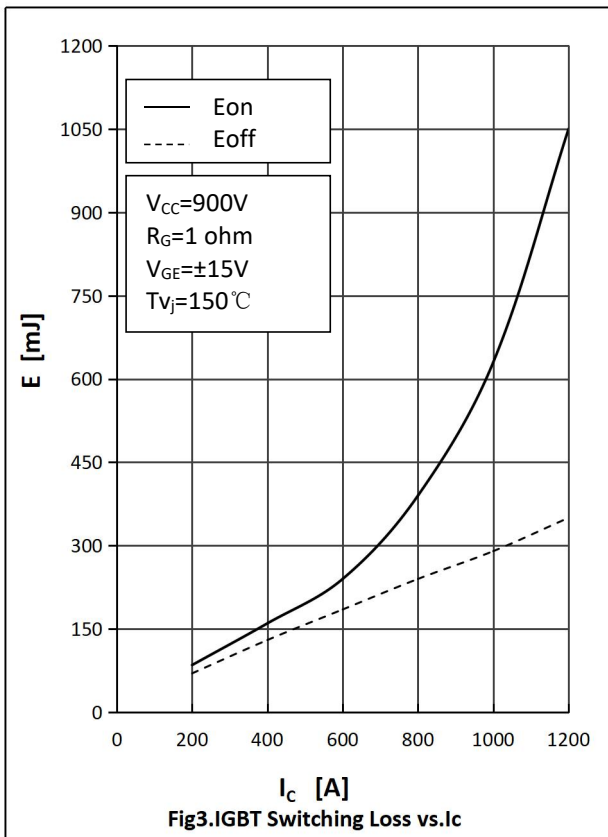
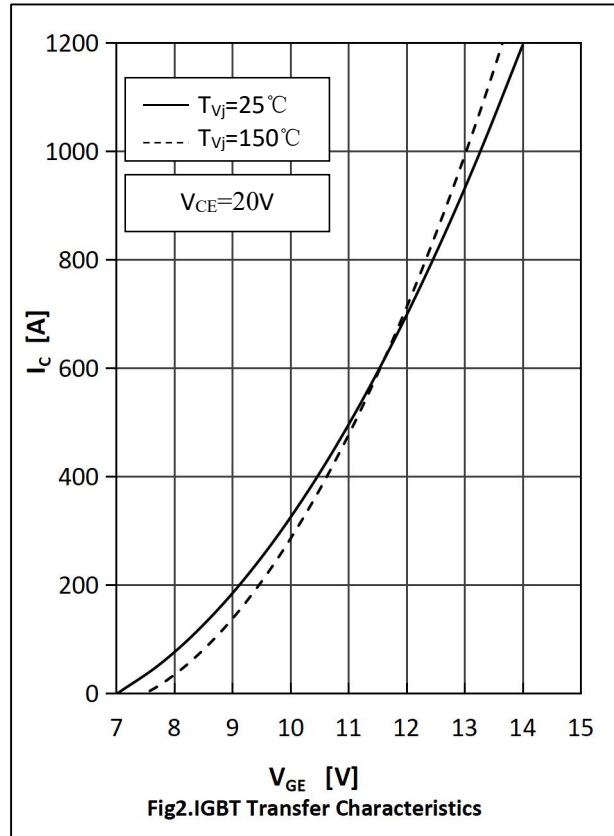
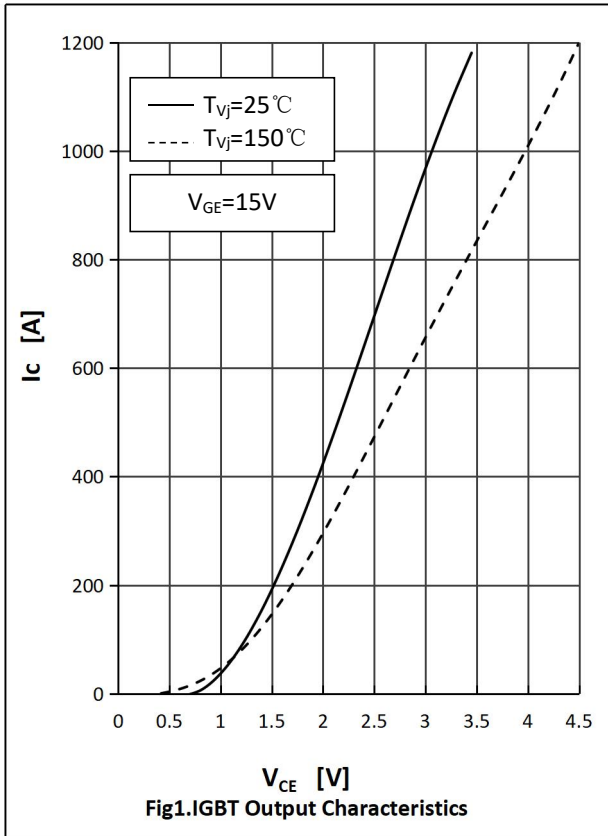
Characteristic values

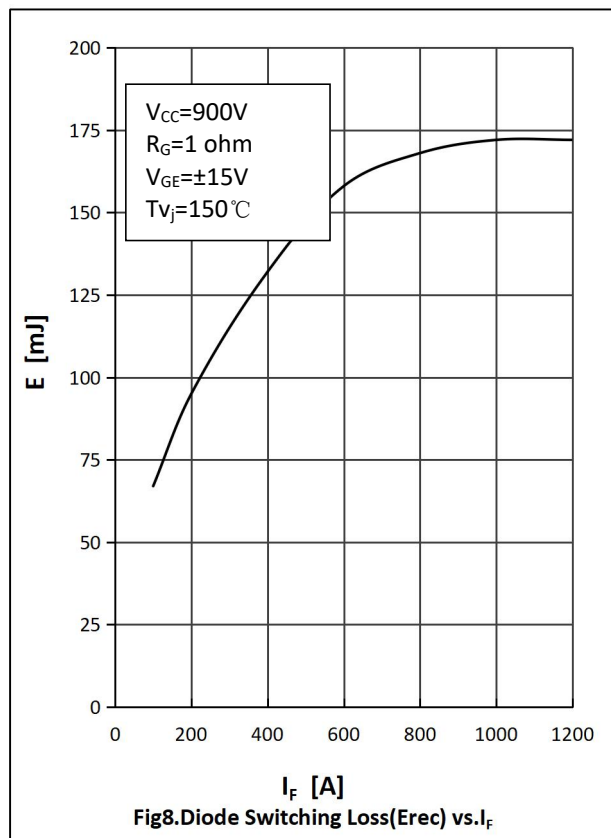
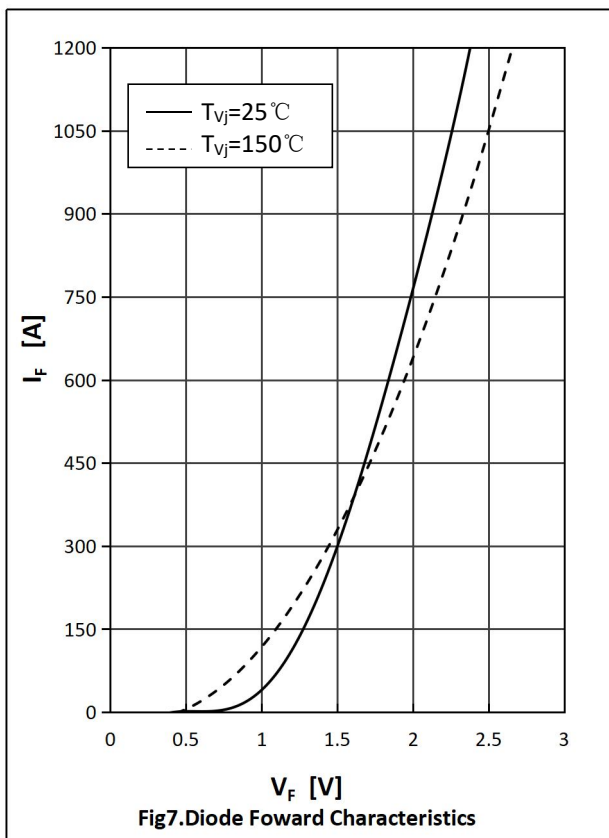
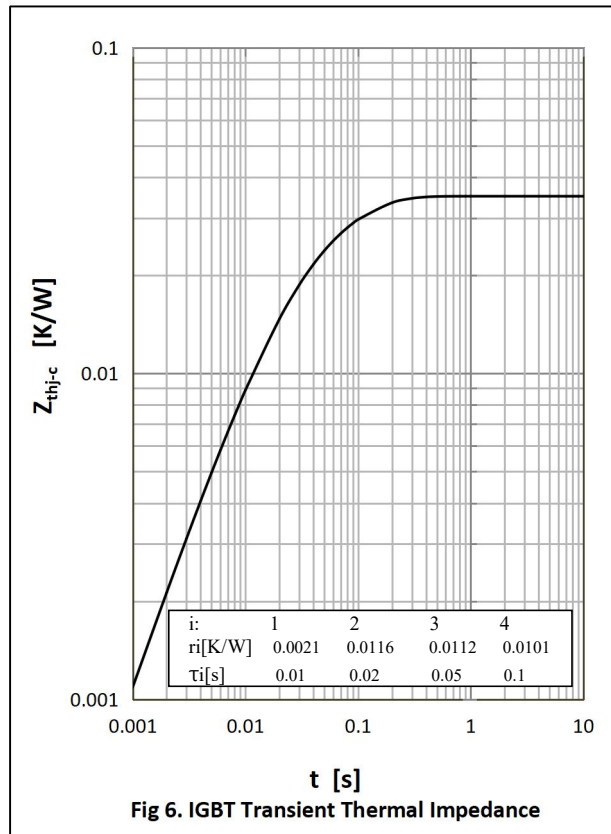
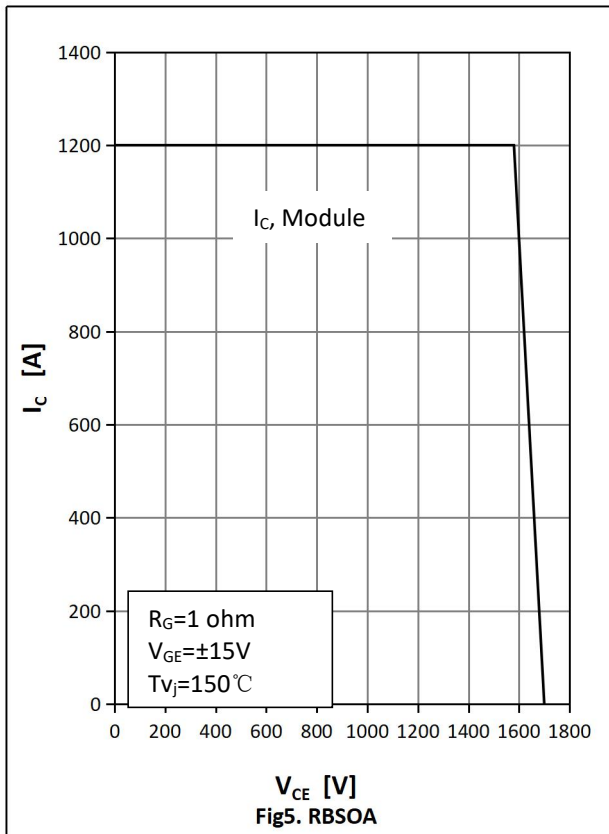
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3 \Omega$	-5		5	%
Power Dissipation	P_{25}			20.0		mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

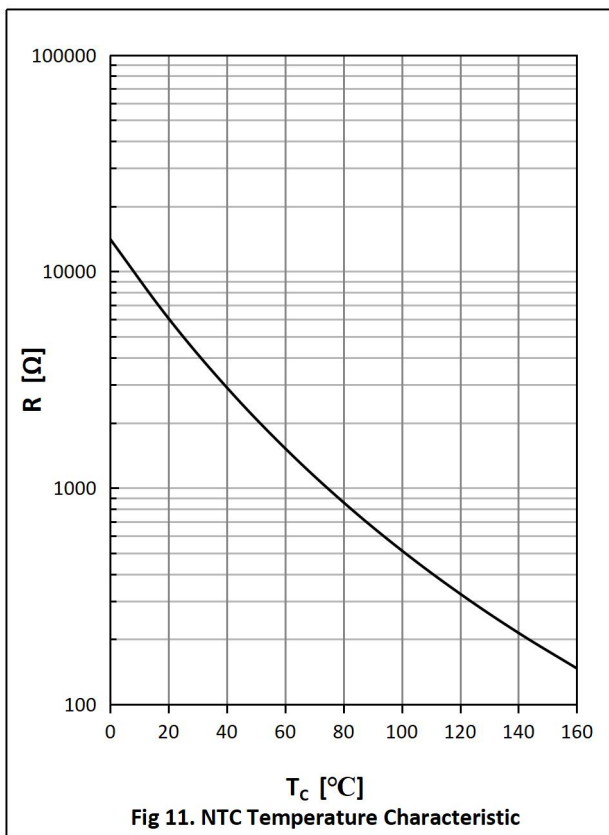
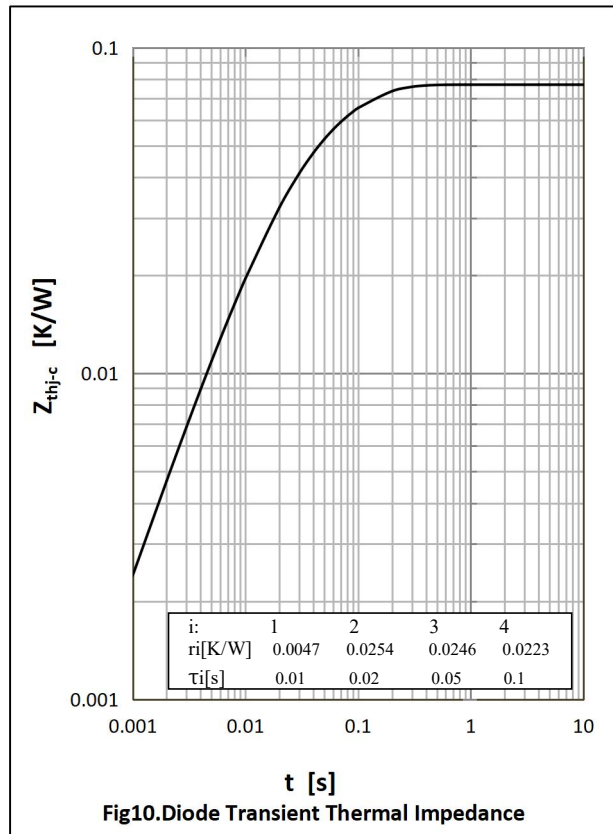
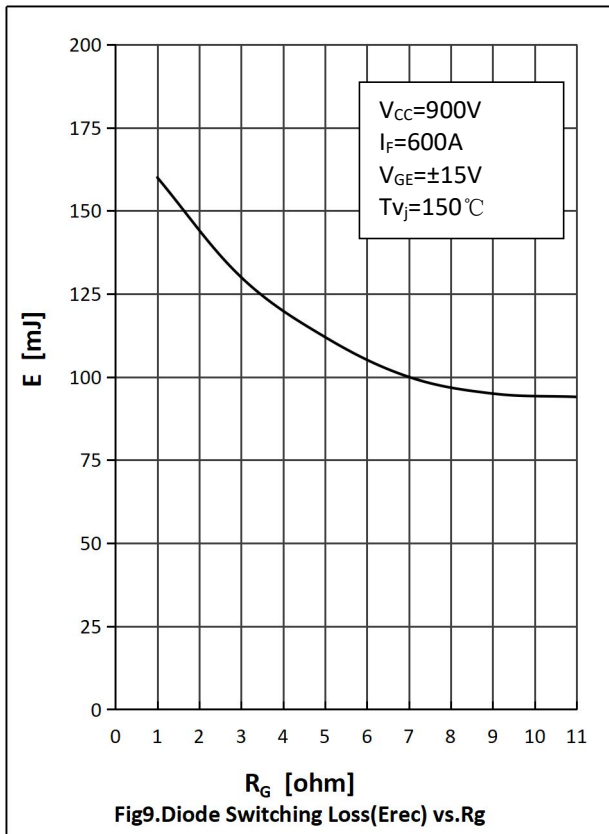
● Module Characteristics

$T_C=25^\circ\text{C}$ unless otherwise specified

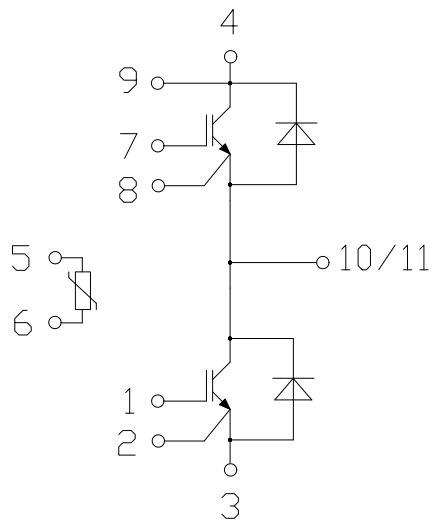
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	4000			V
Maximum Junction Temperature	T_{jmax}				175	$^\circ\text{C}$
Operating Junction Temperature	$T_{vj op}$		-40		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-40		125	$^\circ\text{C}$
Stray Inductance	L_{CE}			20		nH
Module Lead Resistance ,Terminal to Chip	$R_{CC'+EE'}$			1.1		m Ω
Junction-to Case	$R_{\theta jc}$	per IGBT			0.035	K/W
		per Diode			0.077	
Case to Sink (Conductive grease applied)	$R_{\theta cs}$	per IGBT		0.026		K/W
		per Diode		0.058		
		per Module		0.009		
Module Electrodes Torque	M_t	Recommended(M6)	3.0		6.0	N·m
Module-to-Sink Torque	M_s	Recommended(M5)	3.0		6.0	N·m
Weight of Module	G			350		g







● Circuit Diagram



● Package Dimensions

Dimensions in Millimeters

